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1	2	438/197.cccls. and "stack structure" and photoresist and teos	USPAT	2003/07/24 11:58
	387	438/197.cccls.	USPAT	2003/07/16 11:50
	378	438/197.cccls. and substrate	USPAT	2003/07/16 11:58
	89	438/197.cccls. and substrate and "conductive layer"	USPAT	2003/07/16 11:51
	39	438/197.cccls. and substrate and "conductive layer" and "dielectric layer"	USPAT	2003/07/16 11:51
	0	438/197.cccls. and substrate and "conductive layer" and "dielectric layer" and "buried drain"	USPAT	2003/07/16 11:51
	37	438/197.cccls. and substrate and "conductive layer" and "dielectric layer" and "drain"	USPAT	2003/07/16 11:52
	10	438/197.cccls. and substrate and "conductive layer" and "dielectric layer" and "drain" and "insulating layer"	USPAT	2003/07/16 11:52
	3	438/197.cccls. and substrate and "conductive layer" and "dielectric layer" and "drain" and "insulating layer" and "silicon layer"	USPAT	2003/07/16 11:53
	0	438/197.cccls. and substrate and "conductive layer" and "dielectric layer" and "drain" and "insulating layer" and "silicon layer" and cap	USPAT	2003/07/16 11:53
	2	438/197.cccls. and substrate and "conductive layer" and "dielectric layer" and "drain" and "insulating layer" and "silicon layer" and nitride	USPAT	2003/07/16 11:53
	2	438/197.cccls. and substrate and "conductive layer" and "dielectric layer" and "drain" and "insulating layer" and "silicon layer" and nitride and gate	USPAT	2003/07/16 11:53
	6	438/197.cccls. and "non volatile memory"	USPAT	2003/07/16 11:59
	6	438/197.cccls. and "non volatile memory" and substrate	USPAT	2003/07/16 11:59
	6	438/197.cccls. and "non volatile memory" and substrate and conductive	USPAT	2003/07/16 12:05
	2	438/197.cccls. and "non volatile memory" and substrate and conductive and dielectric	USPAT	2003/07/16 12:09
	0	438/197.cccls. and "strip stack"	USPAT	2003/07/16 12:09
	83	438/197.cccls. and "stack"	USPAT	2003/07/16 12:09
	6	438/197.cccls. and "stack structure"	USPAT	2003/07/17 10:42
	6	438/197.cccls. and "stack structure" and semiconductor	USPAT	2003/07/16 12:10
	6	438/197.cccls. and "stack structure" and substrate	USPAT	2003/07/16 12:10
	6	438/197.cccls. and "stack structure" and substrate and gate	USPAT	2003/07/16 12:10
	4	438/197.cccls. and "stack structure" and substrate and gate and dielectric	USPAT	2003/07/16 12:10
	0	438/197.cccls. and "stack structure" and substrate and gate and dielectric and buri\$4	USPAT	2003/07/16 12:11
	4	438/197.cccls. and "stack structure" and substrate and gate and dielectric and drain	USPAT	2003/07/16 12:11
	4	438/197.cccls. and "stack structure" and substrate and gate and dielectric and drain and insulat\$4	USPAT	2003/07/16 12:11
	4	438/197.cccls. and "stack structure" and substrate and gate and dielectric and drain and insulat\$4 and silicon	USPAT	2003/07/16 12:11
	2	438/197.cccls. and "stack structure" and substrate and gate and dielectric and drain and insulat\$4 and silicon and cap	USPAT	2003/07/16 12:12
	1	438/197.cccls. and "stack structure" and substrate and gate and dielectric and drain and insulat\$4 and silicon and cap and line\$4	USPAT	2003/07/16 12:12
	1	438/197.cccls. and "stack structure" and substrate and gate and dielectric and drain and insulat\$4 and silicon and cap and line\$4 and salicide	USPAT	2003/07/16 12:13

1	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat\$4 and silicon and cap and line\$4 and salicide and metal	USPAT	2003/07/17 10:42
4	438/197.ccls. and "stack structure" and photoresist	USPAT	2003/07/24 11:58
1	438/197.ccls. and "stack structure" and substrate and gate and dielectric and drain and insulat\$4 and silicon and cap and line\$4 and salicide and metal and photoresist	USPAT	2003/07/17 10:43